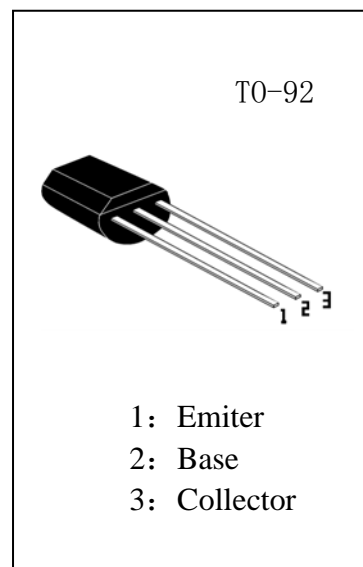


高频晶体管

- 增益带宽高 $f_T=1100\text{MHz}$
- 耗散功率 $P_c=400\text{mW}$

极限参数(Absolute Maximum Ratings) $T_a=25^\circ\text{C}$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	30	V
Collector-Emitter Voltage	V_{ceo}	15	V
Emitter-Base Voltage	V_{ebo}	5	V
Collector Current	I_c	50	mA
Collector Dissipation	P_c	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$


电性能(Electrical Characteristic) $T_a=25^\circ\text{C}$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c=100\mu\text{A}$ $I_e=0$	30			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c=1\text{mA}$ $I_b=0$	15			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e=100\mu\text{A}$ $I_c=0$	5			V
I_{cbo}	Collector Cutoff Current	$V_{cb}=12\text{V}$, $I_e=0$			50	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb}=3\text{V}$, $I_c=0$			50	nA
I_{ceo}	Collector Cutoff Current	$V_{ce}=15\text{V}$, $I_b=0$			10	μA
$V_{ce(sat)}$	Collector-Emitter Saturation Voltage	$I_c=10\text{mA}$, $I_b=1\text{mA}$		0.26	0.5	V
$V_{be(sat)}$	Base-Emitter Saturation Voltage	$I_c=10\text{mA}$, $I_b=1\text{mA}$			1	V
Hfe1	DC Current Gain	$V_{ce}=5\text{V}$, $I_c=1\text{mA}$	28		300	
Hfe2	DC Current Gain	$V_{ce}=5\text{V}$, $I_c=10\text{mA}$	20			
Cob	Output Capacitance	$V_{cb}=10\text{V}$, $I_e=0$, $f=1\text{MHz}$		1.3	1.7	PF
f_T	Current Gain-Bandwidth product	$V_{ce}=10\text{V}$, $I_c=50\text{mA}$,	700	1100		MHz

CLASS	D	E			F	G		H		I		J
Hfe1	28-39	39-45	45-54	54-60	60-72	72-80	80-97	97-108	108-132	132-146	146-198	198-300